

NTTFS4H07NTWG-VB Datasheet

N-Channel 20-V (D-S) MOSFET

PRODUCT SUMMARY

V_{DS} (V)	$R_{DS(on)}$ (Ω)	I_D (A) ^{a, e}	Q_g (Typ)
20	0.0020 at $V_{GS} = 4.5$ V	100	86 nC
	0.0025 at $V_{GS} = 2.5$ V	95	

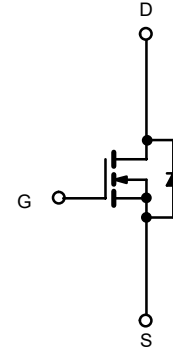
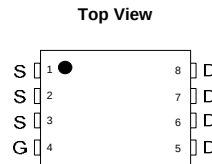
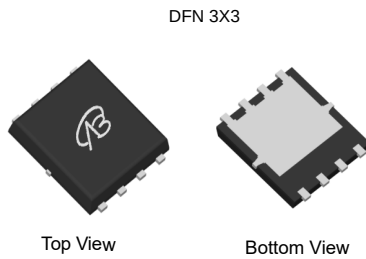
FEATURES

- Trench Power MOSFET
- 100 % R_g and UIS Tested
- Compliant to RoHS Directive 2011/65/EU


RoHS
 COMPLIANT

APPLICATIONS

- OR-ing
- Server
- DC/DC



ABSOLUTE MAXIMUM RATINGS ($T_A = 25$ °C, unless otherwise noted)

Parameter		Symbol	Limit	Unit
Drain-Source Voltage		V_{DS}	20	V
Gate-Source Voltage		V_{GS}	± 12	
Continuous Drain Current ($T_J = 175$ °C)	$T_C = 25$ °C	I_D	100 ^{a, e}	A
	$T_C = 70$ °C		95 ^e	
	$T_A = 25$ °C		35.8 ^{b, c}	
	$T_A = 70$ °C		27 ^{b, c}	
Pulsed Drain Current		I_{DM}	300	
Avalanche Current Pulse		I_{AS}	39	
Single Pulse Avalanche Energy		E_{AS}	94.8	mJ
Continuous Source-Drain Diode Current	$T_C = 25$ °C	I_S	90 ^{a, e}	A
	$T_A = 25$ °C		3.13 ^{b, c}	
Maximum Power Dissipation	$T_C = 25$ °C	P_D	250 ^a	W
	$T_C = 70$ °C		175	
	$T_A = 25$ °C		3.75 ^{b, c}	
	$T_A = 70$ °C		2.63 ^{b, c}	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	- 55 to 175	°C

THERMAL RESISTANCE RATINGS

Parameter		Symbol	Typ.	Max.	Unit
Maximum Junction-to-Ambient ^{b, d}	$t \leq 10$ sec	R_{thJA}	32	40	°C/W
Maximum Junction-to-Case	Steady State	R_{thJC}	0.5	0.6	

Notes:

 a. Based on $T_C = 25$ °C.

b. Surface mounted on 1" x 1" FR4 board.

 c. $t = 10$ sec.

d. Maximum under steady state conditions is 90 °C/W.

e. Calculated based on maximum junction temperature. Package limitation current is 90 A.

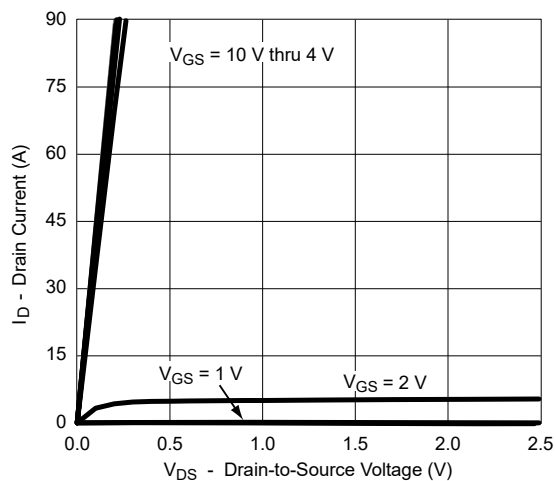
SPECIFICATIONS (T _J = 25 °C, unless otherwise noted)						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} = 0 V, I _D = 250 μA	20			V
V _{DS} Temperature Coefficient	ΔV _{DS} /T _J	I _D = 250 μA		35		mV/°C
V _{GS(th)} Temperature Coefficient	ΔV _{GS(th)} /T _J			- 7.5		
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA	0.5		1.0	V
Gate-Source Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 20 V			± 100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 20 V, V _{GS} = 0 V			1	μA
		V _{DS} = 20 V, V _{GS} = 0 V, T _J = 55 °C			10	
On-State Drain Current ^a	I _{D(on)}	V _{DS} ≥ 5 V, V _{GS} = 10 V	90			A
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = 10 V, I _D = 38.8 A		0.0020		Ω
		V _{GS} = 4.5 V, I _D = 37 A		0.0025		
Forward Transconductance ^a	g _{fs}	V _{DS} = 10 V, I _D = 38.8 A		160		S
Dynamic ^b						
Input Capacitance	C _{iss}	V _{DS} = 10 V, V _{GS} = 0 V, f = 1 MHz		6500		pF
Output Capacitance	C _{oss}			1725		
Reverse Transfer Capacitance	C _{rss}			970		
Total Gate Charge	Q _g	V _{DS} = 10 V, V _{GS} = 10 V, I _D = 38.8 A		171	257	nC
		V _{DS} = 10 V, V _{GS} = 4.5 V, I _D = 28.8 A		81.5	123	
Gate-Source Charge	Q _{gs}			34		
Gate-Drain Charge	Q _{gd}			29		
Gate Resistance	R _g	f = 1 MHz		1.4	2.1	Ω
Turn-On Delay Time	t _{d(on)}	V _{DD} = 10 V, R _L = 0.625 Ω I _D ≅ 24 A, V _{GEN} = 10 V, R _g = 1 Ω		18	27	ns
Rise Time	t _r			11	17	
Turn-Off Delay Time	t _{d(off)}			70	105	
Fall Time	t _f			10	15	
Turn-On Delay Time	t _{d(on)}	V _{DD} = 10 V, R _L = 0.67 Ω I _D ≅ 22.5 A, V _{GEN} = 4.5 V, R _g = 1 Ω		55	83	
Rise Time	t _r			180	270	
Turn-Off Delay Time	t _{d(off)}			55	83	
Fall Time	t _f			12	18	
Drain-Source Body Diode Characteristics						
Continuous Source-Drain Diode Current	I _S	T _C = 25 °C			100	A
Pulse Diode Forward Current ^a	I _{SM}				300	
Body Diode Voltage	V _{SD}	I _S = 22 A		0.8	1.2	V
Body Diode Reverse Recovery Time	t _{rr}	I _F = 20 A, di/dt = 100 A/μs, T _J = 25 °C		52	60	ns
Body Diode Reverse Recovery Charge	Q _{rr}			70.2	105	nC
Reverse Recovery Fall Time	t _a			27		ns
Reverse Recovery Rise Time	t _b			25		

Notes:

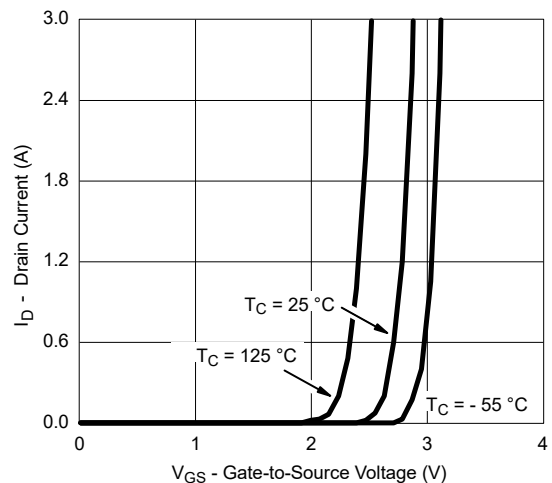
- a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
 b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

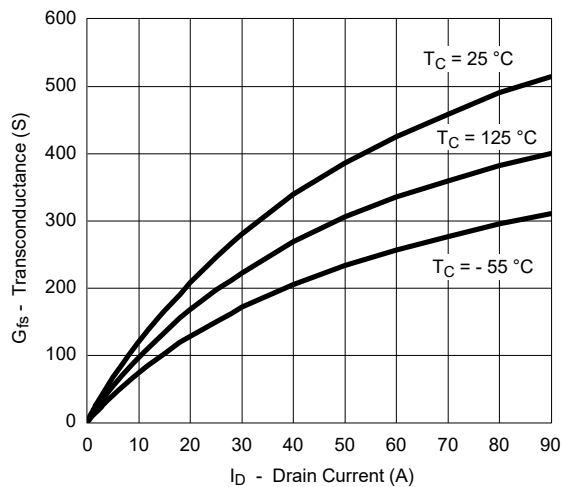
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



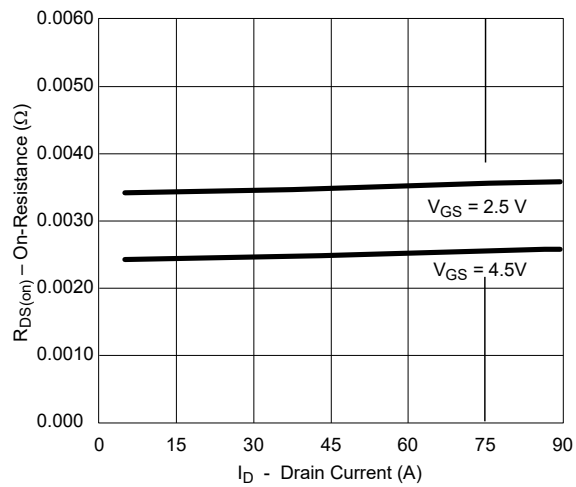
Output Characteristics



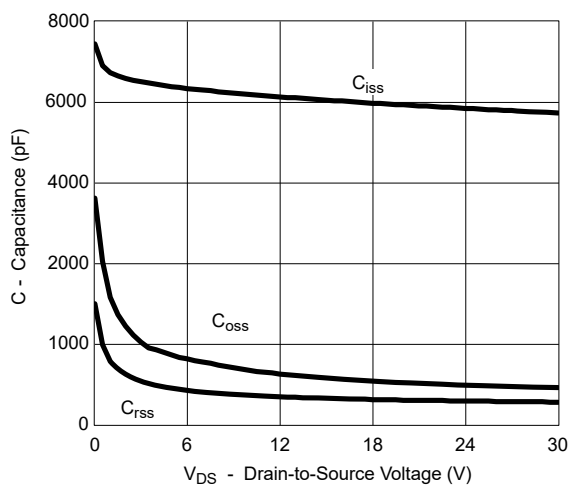
Transfer Characteristics



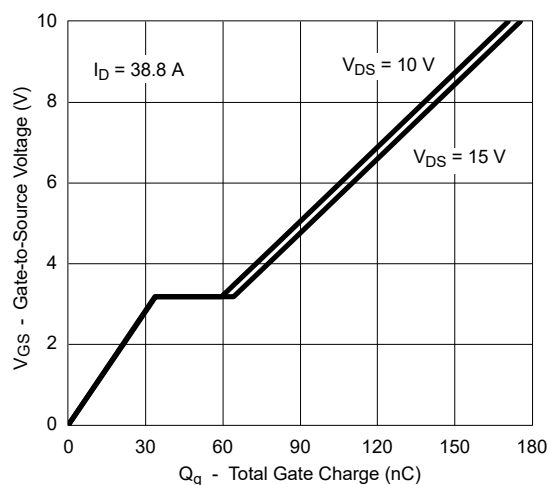
Transconductance



$R_{DS(on)}$ vs. Drain Current

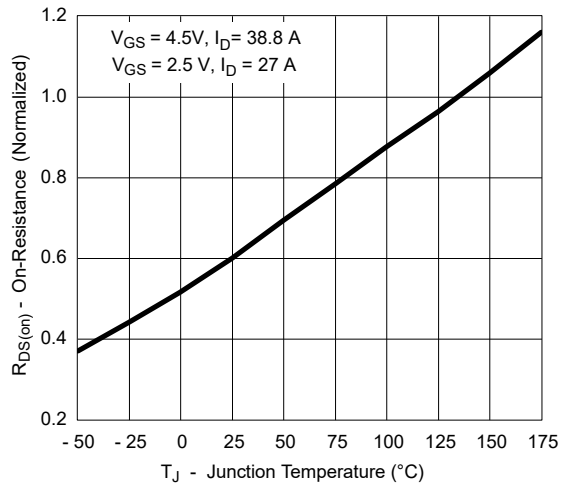


Capacitance

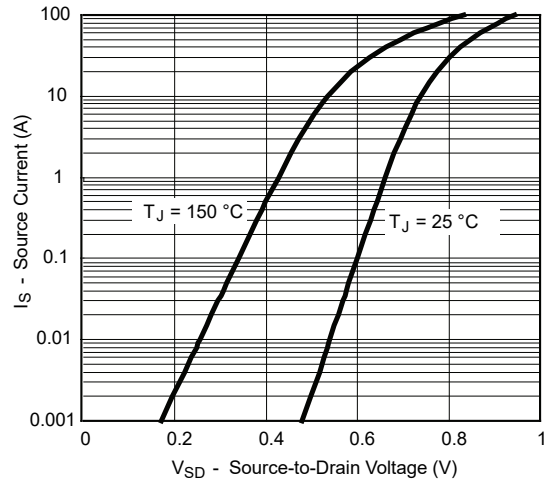


Gate Charge

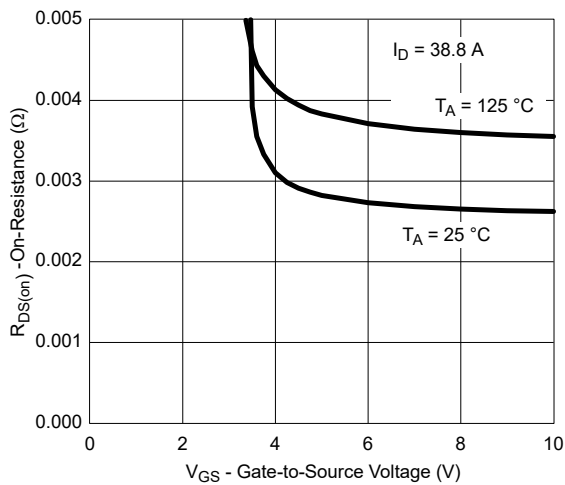
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



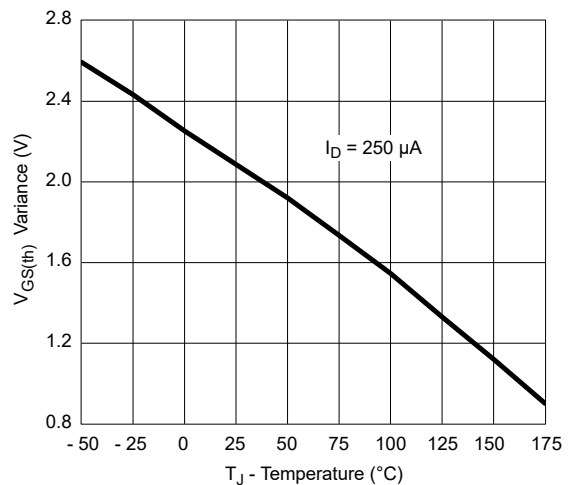
On-Resistance vs. Junction Temperature



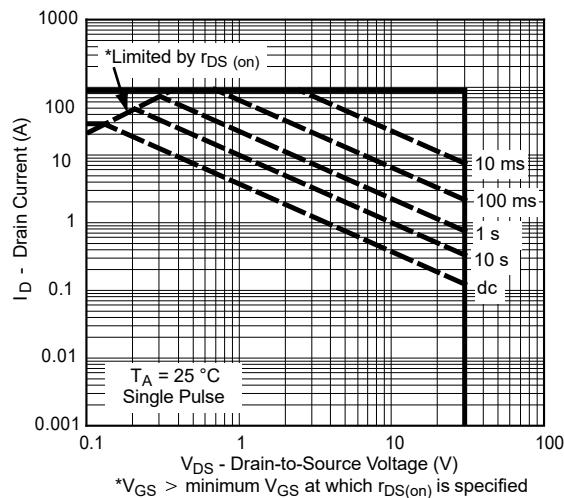
Forward Diode Voltage vs. Temperature



$R_{DS(on)}$ vs. V_{GS} vs. Temperature

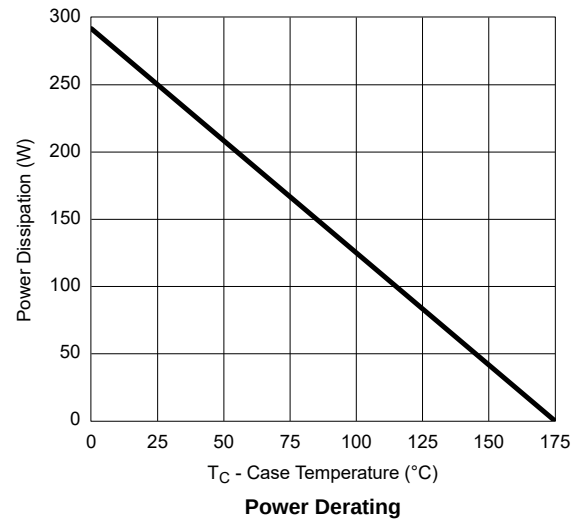
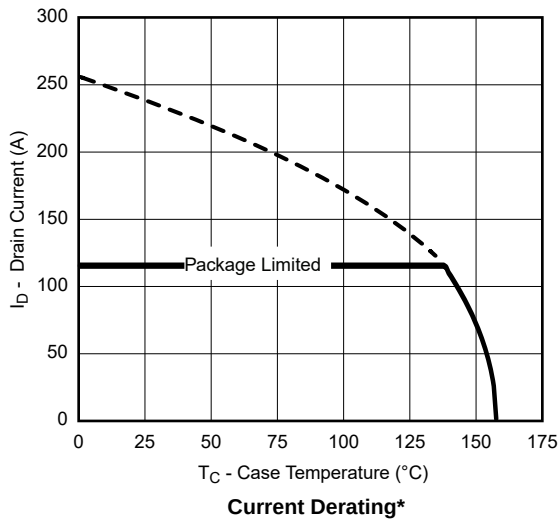


Threshold Voltage

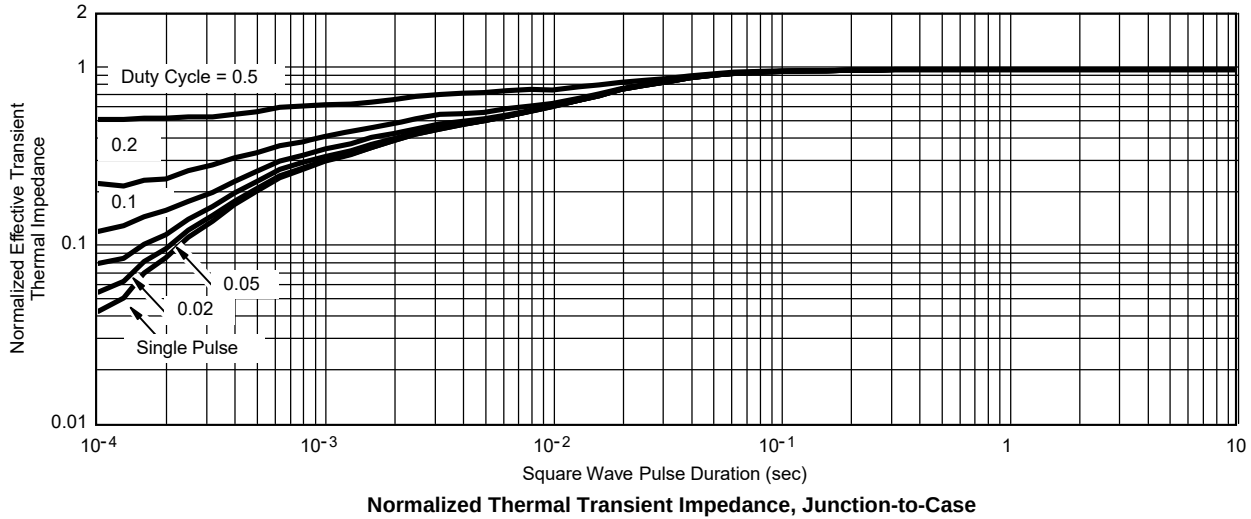


Safe Operating Area, Junction-to-Ambient

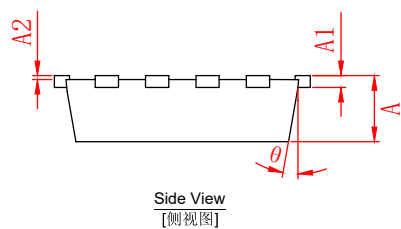
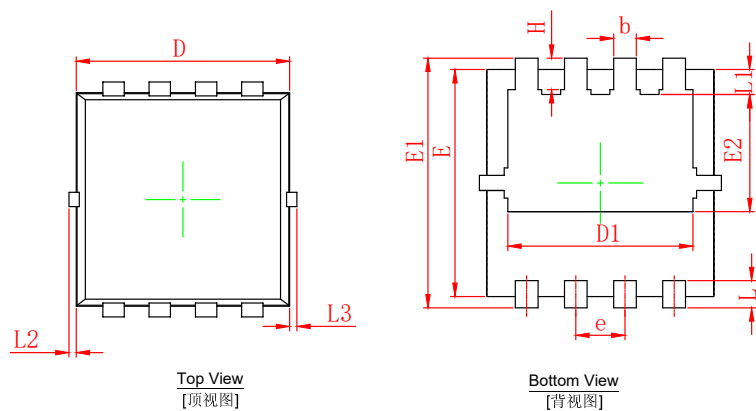
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



*The power dissipation P_D is based on $T_{J(max)} = 175$ °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

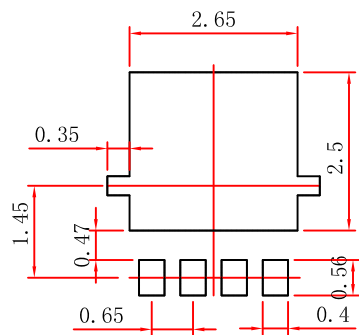


PDFNWB3×3-8L Package Outline Dimensions



Symbol	Dimensions in Millimeters		Dimensions in Inches	
	Min	Max	Min	Max
A	0.650	0.850	0.026	0.033
A1	0.203REF.		0.008REF.	
A2	0~0.05		0~0.002	
D	2.900	3.100	0.114	0.122
D1	2.050	2.550	0.081	0.100
E	2.900	3.100	0.114	0.122
E1	3.150	3.450	0.124	0.136
E2	1.450	1.650	0.057	0.065
b	0.200	0.400	0.008	0.016
e	0.550	0.750	0.022	0.030
L	0.300	0.500	0.012	0.020
L1	0.180	0.480	0.007	0.019
L2	0~0.100		0~0.004	
L3	0~0.100		0~0.004	
H	0.315	0.515	0.012	0.020
Φ	9°	13°	9°	13°

Suggested Pad Layout



- Note:
- 1.Controlling dimension:in millimeters.
 - 2.General tolerance:±0.05mm.
 - 3.The pad layout is for reference purposes only.

Disclaimer

All products due to improve reliability, function or design or for other reasons, product specifications and data are subject to change without notice.

Shenzhen VBsemi Electronics Co., Ltd., branches, agents, employees, and all persons acting on its or their representatives (collectively, the "Shenzhen VBsemi"), assumes no responsibility for any errors, inaccuracies or incomplete data contained in the table or any other any disclosure of any information related to the product.(www.VBsemi.com)

Shenzhen VBsemi makes no guarantee, representation or warranty on the product for any particular purpose of any goods or continuous production. To the maximum extent permitted by applicable law on Shenzhen VBsemi relinquished: (1) any application and all liability arising out of or use of any products; (2) any and all liability, including but not limited to special, consequential damages or incidental ; (3) any and all implied warranties, including a particular purpose, non-infringement and merchantability guarantee.

Statement on certain types of applications are based on knowledge of the product is often used in a typical application of the general product VBsemi Shenzhen demand that the Shenzhen VBsemi of. Statement on whether the product is suitable for a particular application is non-binding. It is the customer's responsibility to verify specific product features in the products described in the specification is appropriate for use in a particular application. Parameter data sheets and technical specifications can be provided may vary depending on the application and performance over time. All operating parameters, including typical parameters must be made by customer's technical experts validated for each customer application. Product specifications do not expand or modify Shenzhen VBsemi purchasing terms and conditions, including but not limited to warranty herein.

Unless expressly stated in writing, Shenzhen VBsemi products are not intended for use in medical, life saving, or life sustaining applications or any other application. Wherein VBsemi product failure could lead to personal injury or death, use or sale of products used in Shenzhen VBsemi such applications using client did not express their own risk. Contact your authorized Shenzhen VBsemi people who are related to product design applications and other terms and conditions in writing.

The information provided in this document and the company's products without a license, express or implied, by estoppel or otherwise, to any intellectual property rights granted to the VBsemi act or document. Product names and trademarks referred to herein are trademarks of their respective representatives will be all.

Material Category Policy

Shenzhen VBsemi Electronics Co., Ltd., hereby certify that all of the products are determined to be RoHS compliant and meets the definition of restrictions under Directive of the European Parliament 2011/65 / EU, 2011 Nian. 6. 8 Ri Yue restrict the use of certain hazardous substances in electrical and electronic equipment (EEE) - modification, unless otherwise specified as inconsistent.(www.VBsemi.com)

Please note that some documents may still refer to Shenzhen VBsemi RoHS Directive 2002/95 / EC. We confirm that all products identified as consistent with the Directive 2002/95 / EC European Directive 2011/65 /.

Shenzhen VBsemi Electronics Co., Ltd. hereby certify that all of its products comply identified as halogen-free halogen-free standards required by the JEDEC JS709A. Please note that some Shenzhenese VBsemi documents still refer to the definition of IEC 61249-2-21, and we are sure that all products conform to confirm compliance with IEC 61249-2-21 standard level JS709A.